

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claim 1 (Currently Amended): A UV sensor comprising:

an incident light window constituting part of the wall of a container; and

a pin-type photodiode disposed inside said container and employed for photoelectrically converting the light that was transmitted through said incident light window,

wherein

said incident light window is composed of borosilicate glass,

said pin-type photodiode comprises a photoabsorption layer formed from $\text{In}_x\text{Ga}_{(1-x)}\text{N}$ ($0 < x < 1$) between an n-type nitride semiconductor layer and a p-type nitride semiconductor layer,

and

each energy gap of said n-type nitride semiconductor layer and p-type nitride semiconductor layer is ~~equal to or~~ larger than the energy gap of said photoabsorption layer.

Claim 2 (Previously Presented): The UV sensor according to claim 1, wherein said incident light window composed of borosilicate glass has a thickness equal to or greater than 200 μm .

Claim 3 (Original): The UV sensor according to claim 1, wherein the composition ratio x of the $\text{In}_x\text{Ga}_{(1-x)}\text{N}$ in said photoabsorption layer is $0 < x < 0.05$.

Claim 4 (Original): The UV sensor according to claim 1, wherein the detection sensitivity of said light with a wavelength of 405 nm is not more than 1/100 of the detection sensitivity of said light with a wavelength of 365 nm.

Claim 5 (Canceled).